**Product data sheet** 

## 1. General description

Planar passivated SCR with sensitive gate in a SOT428 (DPAK) surface mountable plastic package. These devices are intended to be interfaced directly to microcontrollers, logic integrated circuits and other low power gate trigger circuits.

### 2. Features and benefits

- Sensitive gate
- Planar passivated for voltage ruggedness and reliability
- Direct triggering from low power drivers and logic ICs
- Surface mountable package

## 3. Applications

- General purpose switching
- Protection Circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DRM}$	repetitive peak off- state voltage		[1]	-	-	600	V
$V_{RRM}$	repetitive peak reverse voltage			-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$ ; $Fig. 4$ ; $Fig. 5$		-	-	35	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; $T_{mb} \le 111 ^{\circ}\text{C}$ ; Fig. 2; Fig. 3		-	-	4	Α
Static characteristics							
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 7$		-	15	200	μΑ

<sup>[1]</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.





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# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	K	cathode	mb	A <del>- □  </del> K
2	Α	anode[1]		G sym037
3	G	gate		ŕ
mb	A	mounting base; connected to anode	1 3	
			DPAK (SOT428)	

<sup>[1]</sup> It is not possible to connect to pin 2 of the SOT428 package.

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
BT150S-600R	DPAK	plastic single-ended surface-mounted package (DPAK); 3 leads (one lead cropped)	SOT428			

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# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		[1]	-	600	V
$V_{RRM}$	repetitive peak reverse voltage			-	600	V
I <sub>T(AV)</sub>	average on-state current	half sine wave; T <sub>mb</sub> ≤ 111 °C; <u>Fig. 1</u>		-	2.5	Α
I <sub>T(RMS)</sub>	RMS on-state current	half sine wave; T <sub>mb</sub> ≤ 111 °C; <u>Fig. 2;</u> <u>Fig. 3</u>		-	4	А
I <sub>TSM</sub>	non-repetitive peak on-state current	half sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 10 \text{ ms}$ ; Fig. 4; Fig. 5		-	35	А
		half sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 8.3  \text{ms}$		-	38	А
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN		-	6.1	A <sup>2</sup> s
dI <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 10 \text{ A}$ ; $I_G = 50 \text{ mA}$ ; $dI_G/dt = 50 \text{ mA}/$ µs		-	50	A/µs
I <sub>GM</sub>	peak gate current			-	2	Α
$V_{RGM}$	peak reverse gate voltage			-	5	V
$P_{GM}$	peak gate power			-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period		-	0.5	W
T <sub>stg</sub>	storage temperature			-40	150	°C
Tj	junction temperature		[2]	-	125	°C

<sup>[1]</sup> Although not recommended, off-state voltages up to 800V may be applied without damage, but the thyristor may switch to the on-state. The rate of rise of current should not exceed 15 A/µs.

<sup>[2]</sup> Operation above 110°C may require the use of a gate to cathode resistor of  $1k\Omega$  or less.

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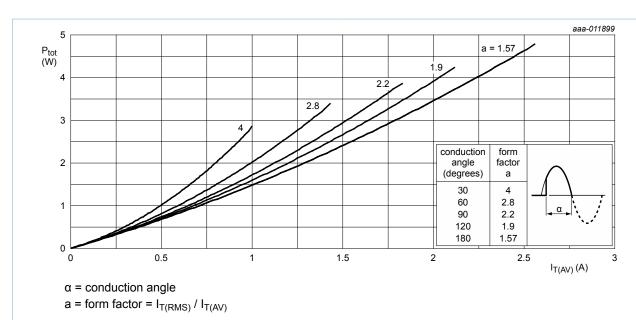


Fig. 1. Total power dissipation as a function of average on-state current; maximum values

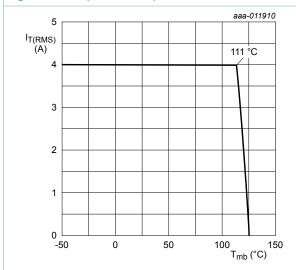
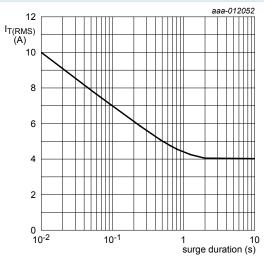


Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 111 ^{\circ}\text{C}$ 

Fig. 3. RMS on-state current as a function of surge duration; maximum values

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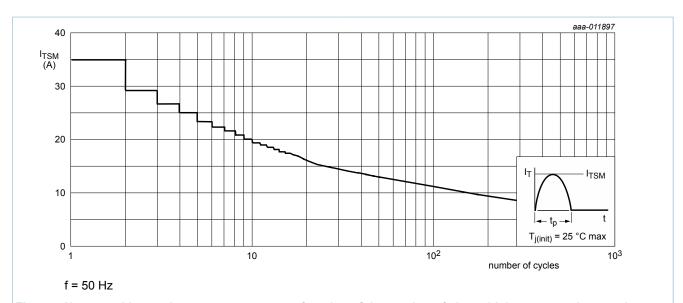


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

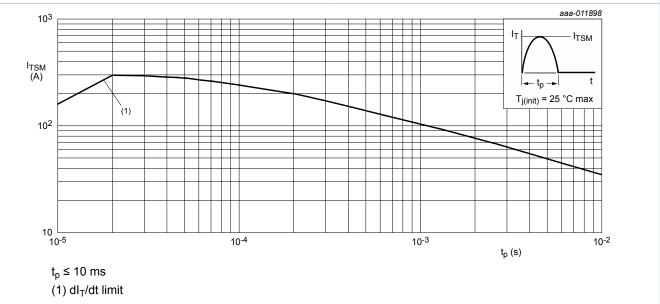


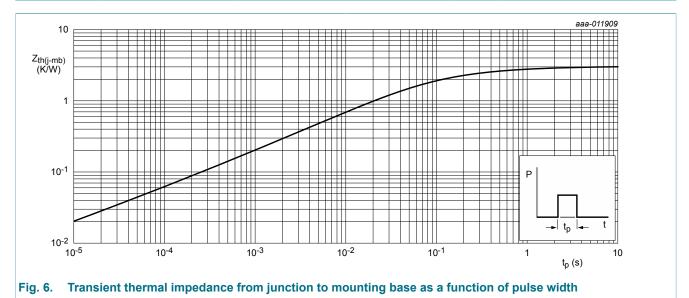
Fig. 5. Non-repetitive peak on-state current as a function of pulse width for sinusoidal currents; maximum values

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## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance from junction to mounting base	Fig. 6	-	-	3	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	Device mounted on an FR4 Printed- Circuit Board (PCB), single-sided copper, tin-plated and standard footprint	-	75	-	K/W



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## 9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	racteristics		'			
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	-	15	200	μA
IL	latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T_j = 25 \text{ °C}; Fig. 8$	-	0.17	10	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	0.1	6	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 5 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.23	1.8	V
V <sub>GT</sub>	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.4	1	V
		$V_D = 600 \text{ V}; I_T = 0.1 \text{ A}; T_j = 110 °C;$ Fig. 11	0.1	0.2	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
I <sub>R</sub>	reverse current	V <sub>R</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
Dynamic c	haracteristics		'			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $R_{GK}$ = 100 Ω; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; Fig. 12	-	50	-	V/µs
t <sub>gt</sub>	gate-controlled turn-on time	$I_{TM}$ = 10 A; $V_D$ = 600 V; $I_G$ = 5 mA; $dI_G/$ dt = 0.2 A/ $\mu$ s; $T_j$ = 25 °C	-	2	-	μs
t <sub>q</sub>	commutated turn-off time	$V_{DM}$ = 402 V; $T_j$ = 125 °C; $I_{TM}$ = 8 A; $V_R$ = 10 V; $(dI_T/dt)_M$ = 10 A/µs; $dV_D/dt$ = 2 V/µs; $R_{GK}$ = 1 k $\Omega$ ; $(V_{DM}$ = 67% of $V_{DRM})$	-	100	-	μs

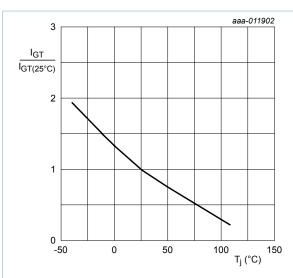


Fig. 7. Normalized gate trigger current as a function of junction temperature

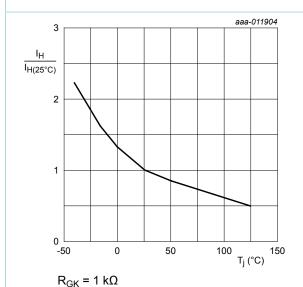
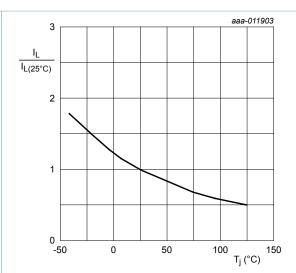
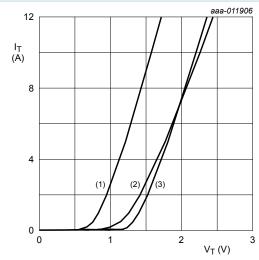


Fig. 9. Normalized holding current as a function of junction temperature



 $R_{GK} = 1 k\Omega$ 

Fig. 8. Normalized latching current as a function of junction temperature



 $V_0 = 1.26 \text{ V}; R_s = 0.099 \Omega$ 

(1) T<sub>i</sub> = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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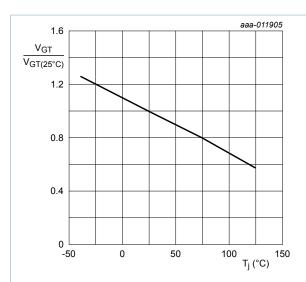


Fig. 11. Normalized gate trigger voltage as a function of junction temperature

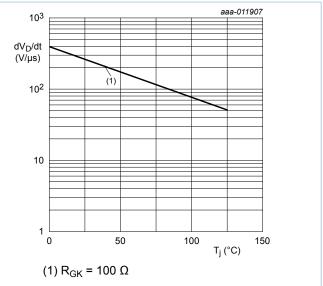


Fig. 12. Critical rate of rise of off-state voltage as a function of junction temperature; typical values

## 10. Package outline

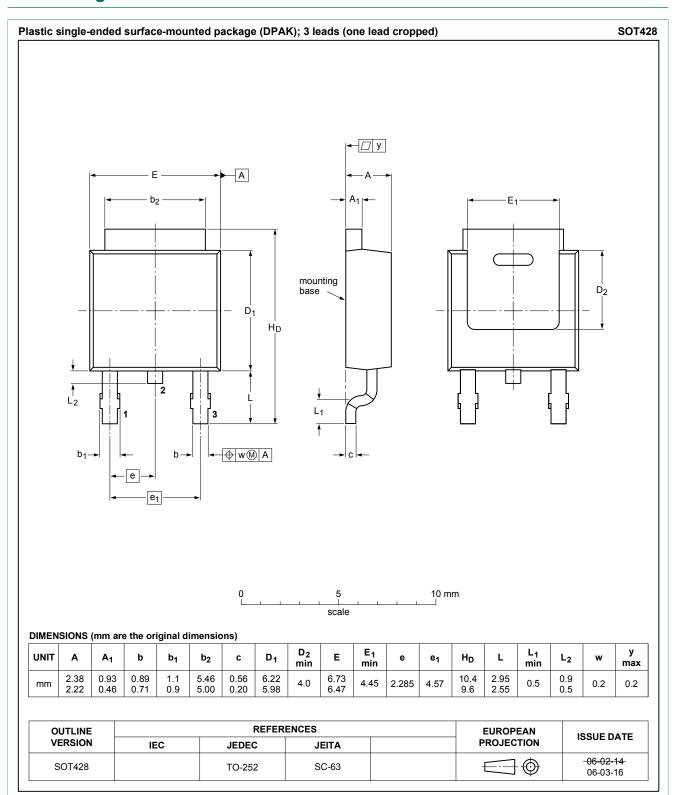
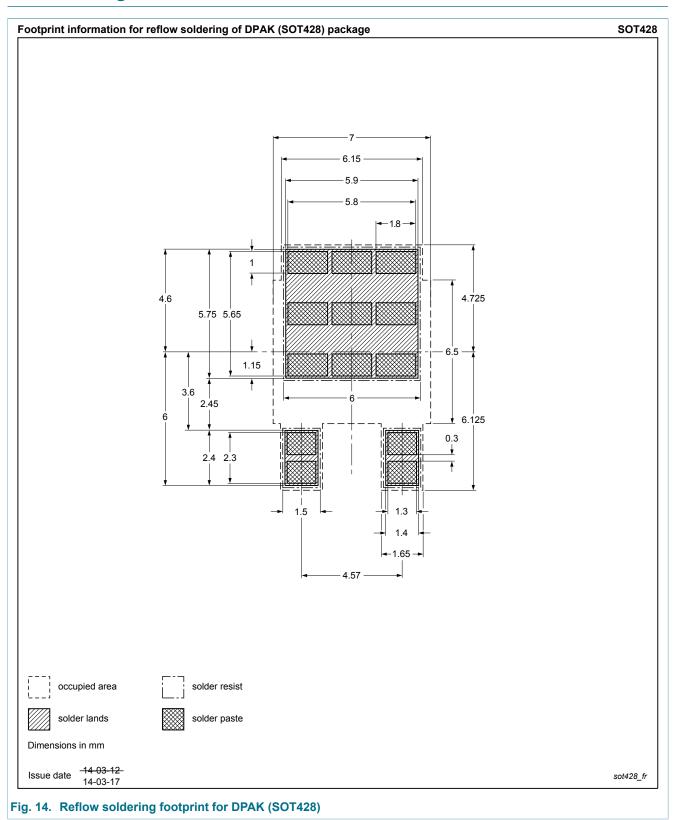


Fig. 13. Package outline DPAK (SOT428)

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# 11. Soldering



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### 12. Legal information

#### 12.1 Data sheet status

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Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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